

## Preliminary datasheet

### EconoPIM™2 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

#### Features

- Electrical features
  - $V_{CES} = 1200\text{ V}$
  - $I_{C\text{nom}} = 100\text{ A} / I_{CRM} = 200\text{ A}$
  - Low  $V_{CESat}$
  - Overload operation up to  $175^\circ\text{C}$
  - TRENCHSTOP™ IGBT7
- Mechanical features
  - $\text{Al}_2\text{O}_3$  substrate with low thermal resistance
  - Copper base plate
  - Integrated NTC temperature sensor
  - PressFIT contact technology



Typical appearance

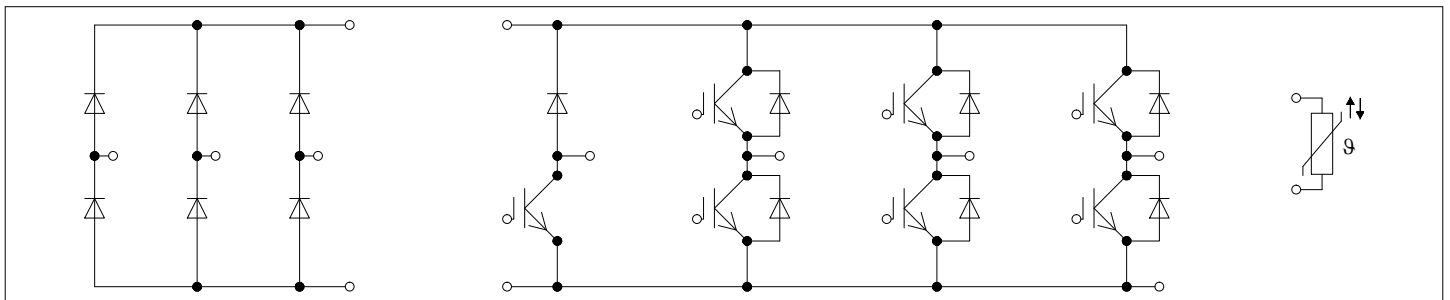
#### Potential applications

- Servo drives
- Auxiliary inverters
- Motor drives

#### Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

#### Description



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**1 Package**

## 1 Package

**Table 1 Insulation coordination**

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	$V_{ISOL}$	RMS, $f = 50 \text{ Hz}$ , $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal Isolation		basic insulation (class 1, IEC 61140)	$Al_2O_3$	
Creepage distance	$d_{Creep}$	terminal to heatsink	10.0	mm
Clearance	$d_{Clear}$	terminal to heatsink	7.5	mm
Comparative tracking index	$CTI$		> 200	
RTI Elec.	$RTI$	housing	140	°C

**Table 2 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	$L_{SCE}$			35		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25^\circ\text{C}$ , per switch		2.5		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$ , per switch		4.3		mΩ
Storage temperature	$T_{stg}$		-40		125	°C
Mounting torque for modul mounting	$M$	- Mounting according to valid application note	M5, Screw	3	6	Nm
Weight	$G$			180		g

*Note: The current under continuous operation is limited to 80A rms in the main AC and DC power terminals and limited to 50A rms per connector pin.*

## 2 IGBT, Inverter

**Table 3 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	$V_{CES}$	$T_{vj} = 25^\circ\text{C}$	1200	V
Continous DC collector current	$I_{CDC}$	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 95^\circ\text{C}$	100	A
Repetitive peak collector current	$I_{CRM}$	$t_p = 1 \text{ ms}$	200	A
Gate-emitter peak voltage	$V_{GES}$		±20	V

**Table 4** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 100\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.50	TBD	V
			$T_{vj} = 125\ ^\circ C$	1.64		
			$T_{vj} = 175\ ^\circ C$	1.72		
Gate threshold voltage	$V_{GEth}$	$I_C = 2.5\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.15	5.80	6.45	V
Gate charge	$Q_G$	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$		1.8		$\mu C$
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25\ ^\circ C$		1.5		$\Omega$
Input capacitance	$C_{ies}$	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		21.7		nF
Reverse transfer capacitance	$C_{res}$	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		0.076		nF
Collector-emitter cut-off current	$I_{CES}$	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$		0.01	mA
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			100	nA
Turn-on delay time (inductive load)	$t_{don}$	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.171		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.185		
			$T_{vj} = 175\ ^\circ C$	0.190		
Rise time (inductive load)	$t_r$	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.050		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.055		
			$T_{vj} = 175\ ^\circ C$	0.058		
Turn-off delay time (inductive load)	$t_{doff}$	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.324		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.433		
			$T_{vj} = 175\ ^\circ C$	0.494		
Fall time (inductive load)	$t_f$	$I_C = 100\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.093		$\mu s$
			$T_{vj} = 125\ ^\circ C$	0.183		
			$T_{vj} = 175\ ^\circ C$	0.245		
Turn-on energy loss per pulse	$E_{on}$	$I_C = 100\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 4.3\ \Omega, di/dt = 1450\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	10.4		mJ
			$T_{vj} = 125\ ^\circ C$	15.3		
			$T_{vj} = 175\ ^\circ C$	17.6		
Turn-off energy loss per pulse	$E_{off}$	$I_C = 100\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 4.3\ \Omega, dv/dt = 2850\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	6.42		mJ
			$T_{vj} = 125\ ^\circ C$	9.95		
			$T_{vj} = 175\ ^\circ C$	12.3		
SC data	$I_{SC}$	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 8\ \mu s, T_{vj} = 150\ ^\circ C$	370		A
			$t_p \leq 7\ \mu s, T_{vj} = 175\ ^\circ C$	350		

**Table 4** Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	$R_{thJC}$	per IGBT			0.371	K/W
Thermal resistance, case to heatsink	$R_{thCH}$	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}^2\text{K})$		0.135		K/W
Temperature under switching conditions	$T_{vj\text{op}}$		-40		175	°C

Note:  $T_{vj\text{op}} > 150^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

### 3 Diode, Inverter

**Table 5** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25^\circ\text{C}$	1200	V	
Continuous DC forward current	$I_F$		100	A	
Repetitive peak forward current	$I_{FRM}$	$t_P = 1 \text{ ms}$	200	A	
$I^2t$ - value	$I^2t$	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	1000	$\text{A}^2\text{s}$
			$T_{vj} = 175^\circ\text{C}$	930	

**Table 6** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	$V_F$	$I_F = 100 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.72	TBD	V
			$T_{vj} = 125^\circ\text{C}$		1.59		
			$T_{vj} = 175^\circ\text{C}$		1.52		
Peak reverse recovery current	$I_{RM}$	$V_R = 600 \text{ V}, I_F = 100 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1450 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		58.2		A
			$T_{vj} = 125^\circ\text{C}$		74.3		
			$T_{vj} = 175^\circ\text{C}$		82.4		
Recovered charge	$Q_r$	$V_R = 600 \text{ V}, I_F = 100 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1450 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		9.83		$\mu\text{C}$
			$T_{vj} = 125^\circ\text{C}$		15.9		
			$T_{vj} = 175^\circ\text{C}$		20.1		

**Table 6** Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	$E_{rec}$	$V_R = 600\text{ V}$ , $I_F = 100\text{ A}$ , $V_{GE} = -15\text{ V}$ , $-di_F/dt = 1450\text{ A}/\mu\text{s}$ ( $T_{vj} = 175\text{ °C}$ )	$T_{vj} = 25\text{ °C}$	3.31		mJ
			$T_{vj} = 125\text{ °C}$	5.01		
			$T_{vj} = 175\text{ °C}$	6.45		
Thermal resistance, junction to case	$R_{thJC}$	per diode			0.592	K/W
Thermal resistance, case to heatsink	$R_{thCH}$	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.148		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note:  $T_{vj\text{ op}} > 150\text{ °C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 4 Diode, Rectifier

**Table 7** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25\text{ °C}$	1600	V	
Maximum RMS forward current per chip	$I_{FRMSM}$	$T_C = 110\text{ °C}$	100	A	
Maximum RMS current at rectifier output	$I_{RMSM}$	$T_C = 110\text{ °C}$	100	A	
Surge forward current	$I_{FSM}$	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	745	A
			$T_{vj} = 150\text{ °C}$	515	
$I^2t$ - value	$I^2t$	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	2780	A <sup>2</sup> s
			$T_{vj} = 150\text{ °C}$	1330	

**Table 8** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	$V_F$	$I_F = 100\text{ A}$ , $T_{vj} = 150\text{ °C}$		1.16		V
Reverse current	$I_r$	$T_{vj} = 150\text{ °C}$ , $V_R = 1600\text{ V}$		1		mA
Thermal resistance, junction to case	$R_{thJC}$	per diode			0.697	K/W
Thermal resistance, case to heatsink	$R_{thCH}$	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.153		K/W

**Table 8** Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

## 5 IGBT, Brake-Chopper

**Table 9** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	$V_{CES}$	$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC collector current	$I_{CDC}$	$T_{vj\ max} = 175\text{ °C}$ $T_C = 115\text{ °C}$	50	A
Repetitive peak collector current	$I_{CRM}$	$t_p = 1\text{ ms}$	100	A
Gate-emitter peak voltage	$V_{GES}$		±20	V

**Table 10** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.50	TBD	V
			$T_{vj} = 125\text{ °C}$	1.64		
			$T_{vj} = 175\text{ °C}$	1.72		
Gate threshold voltage	$V_{GEth}$	$I_C = 1.28\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25\text{ °C}$	5.15	5.80	6.45	V
Gate charge	$Q_G$	$V_{GE} = \pm 15\text{ V}, V_{CE} = 600\text{ V}$		0.92		µC
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25\text{ °C}$		0		Ω
Input capacitance	$C_{ies}$	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		11.1		nF
Reverse transfer capacitance	$C_{res}$	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		0.039		nF
Collector-emitter cut-off current	$I_{CES}$	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$			0.008	mA
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25\text{ °C}$			100	nA
Turn-on delay time (inductive load)	$t_{don}$	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 8.2\text{ }\Omega$	$T_{vj} = 25\text{ °C}$	0.060		µs
			$T_{vj} = 125\text{ °C}$	0.062		
			$T_{vj} = 175\text{ °C}$	0.063		
Rise time (inductive load)	$t_r$	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 8.2\text{ }\Omega$	$T_{vj} = 25\text{ °C}$	0.036		µs
			$T_{vj} = 125\text{ °C}$	0.040		
			$T_{vj} = 175\text{ °C}$	0.042		

**Table 10** Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off delay time (inductive load)	$t_{doff}$	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.290		$\mu\text{s}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.380		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.420		
Fall time (inductive load)	$t_f$	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.110		$\mu\text{s}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.200		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.270		
Turn-on energy loss per pulse	$E_{on}$	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, L_\sigma = 35\text{ nH}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 8.2\ \Omega, di/dt = 800\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	5.35		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	7.04		
			$T_{vj} = 175\text{ }^\circ\text{C}$	8		
Turn-off energy loss per pulse	$E_{off}$	$I_C = 50\text{ A}, V_{CE} = 600\text{ V}, L_\sigma = 35\text{ nH}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 8.2\ \Omega, dv/dt = 2900\text{ V}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	3.33		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	5.32		
			$T_{vj} = 175\text{ }^\circ\text{C}$	6.58		
SC data	$I_{SC}$	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 8\ \mu\text{s}, T_{vj} = 150\text{ }^\circ\text{C}$	190		A
			$t_P \leq 7\ \mu\text{s}, T_{vj} = 175\text{ }^\circ\text{C}$	180		
Thermal resistance, junction to case	$R_{thJC}$	per IGBT			0.580	K/W
Thermal resistance, case to heatsink	$R_{thCH}$	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}^2\text{K})$		0.147		K/W
Temperature under switching conditions	$T_{vjop}$		-40		175	$^\circ\text{C}$

Note:  $T_{vjop} > 150\text{ }^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 6 Diode, Brake-Chopper

**Table 11** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25\text{ }^\circ\text{C}$	1200	V
Continuous DC forward current	$I_F$		35	A
Repetitive peak forward current	$I_{FRM}$	$t_P = 1\text{ ms}$	70	A



**Table 11** Maximum rated values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
I <sup>2</sup> t - value	I <sup>2</sup> t	t <sub>p</sub> = 10 ms, V <sub>R</sub> = 0 V	T <sub>vj</sub> = 150 °C	125		A <sup>2</sup> s
			T <sub>vj</sub> = 175 °C	95		

**Table 12** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 35 A, V <sub>GE</sub> = 0 V	T <sub>vj</sub> = 25 °C	1.72	TBD	V
			T <sub>vj</sub> = 125 °C	1.59		
			T <sub>vj</sub> = 175 °C	1.52		
Peak reverse recovery current	I <sub>RM</sub>	V <sub>R</sub> = 600 V, I <sub>F</sub> = 35 A, V <sub>GE</sub> = -15 V, -di <sub>F</sub> /dt = 700 A/μs (T <sub>vj</sub> = 175 °C)	T <sub>vj</sub> = 25 °C	20.1		A
			T <sub>vj</sub> = 125 °C	25.9		
			T <sub>vj</sub> = 175 °C	29.8		
Recovered charge	Q <sub>r</sub>	V <sub>R</sub> = 600 V, I <sub>F</sub> = 35 A, V <sub>GE</sub> = -15 V, -di <sub>F</sub> /dt = 700 A/μs (T <sub>vj</sub> = 175 °C)	T <sub>vj</sub> = 25 °C	2.66		μC
			T <sub>vj</sub> = 125 °C	4.73		
			T <sub>vj</sub> = 175 °C	6.94		
Reverse recovery energy	E <sub>rec</sub>	V <sub>R</sub> = 600 V, I <sub>F</sub> = 35 A, V <sub>GE</sub> = -15 V, -di <sub>F</sub> /dt = 700 A/μs (T <sub>vj</sub> = 175 °C)	T <sub>vj</sub> = 25 °C	0.95		mJ
			T <sub>vj</sub> = 125 °C	1.72		
			T <sub>vj</sub> = 175 °C	2.38		
Thermal resistance, junction to case	R <sub>thJC</sub>	per diode			1.11	K/W
Thermal resistance, case to heatsink	R <sub>thCH</sub>	per diode, λ <sub>grease</sub> = 1 W/(m*K)		0.176		K/W
Temperature under switching conditions	T <sub>vj op</sub>		-40		175	°C

Note: T<sub>vj op</sub> > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 7 NTC-Thermistor

**Table 13** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R <sub>25</sub>	T <sub>NTC</sub> = 25 °C		5		kΩ
Deviation of R <sub>100</sub>	ΔR/R	T <sub>NTC</sub> = 100 °C, R <sub>100</sub> = 493 Ω	-5		5	%
Power dissipation	P <sub>25</sub>	T <sub>NTC</sub> = 25 °C			20	mW

**Table 13**                      **Characteristic values (continued)**

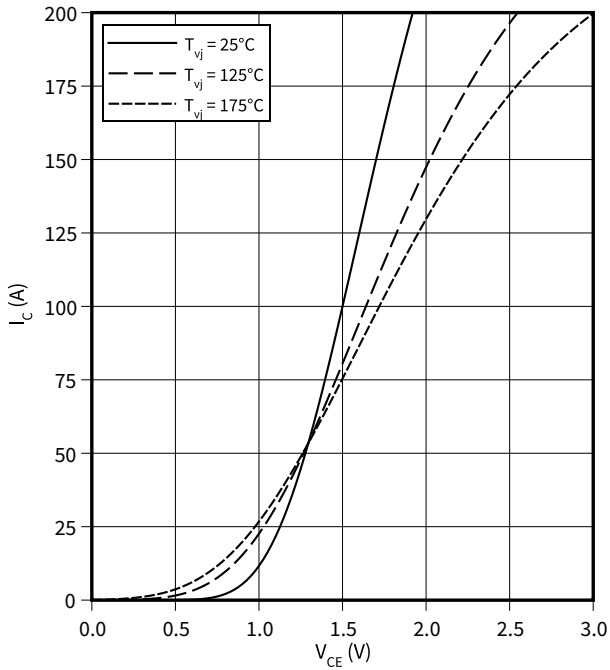
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

Note:                      *Specification according to the valid application note.*

## 8 Characteristics diagrams

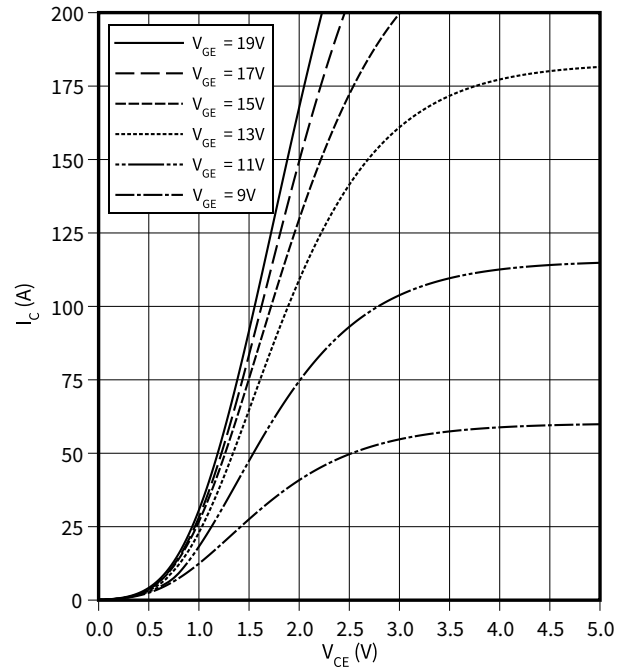
**output characteristic (typical), IGBT, Inverter**

$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



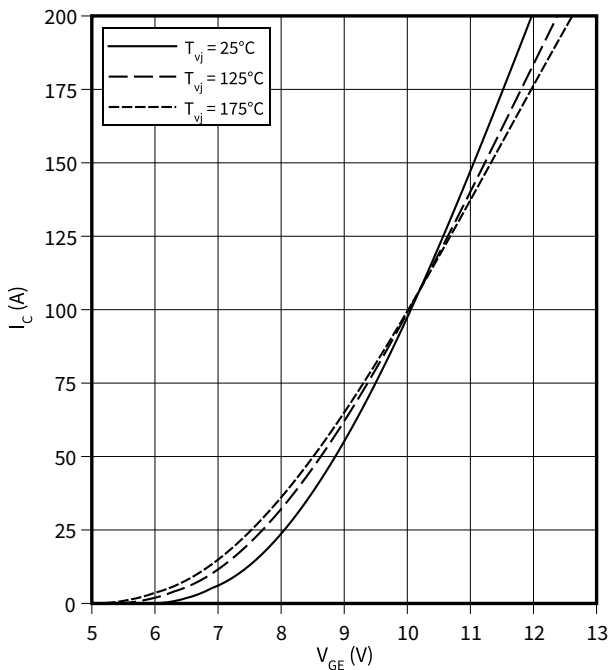
**output characteristic (typical), IGBT, Inverter**

$I_C = f(V_{CE})$   
 $T_{vj} = 175\text{ °C}$



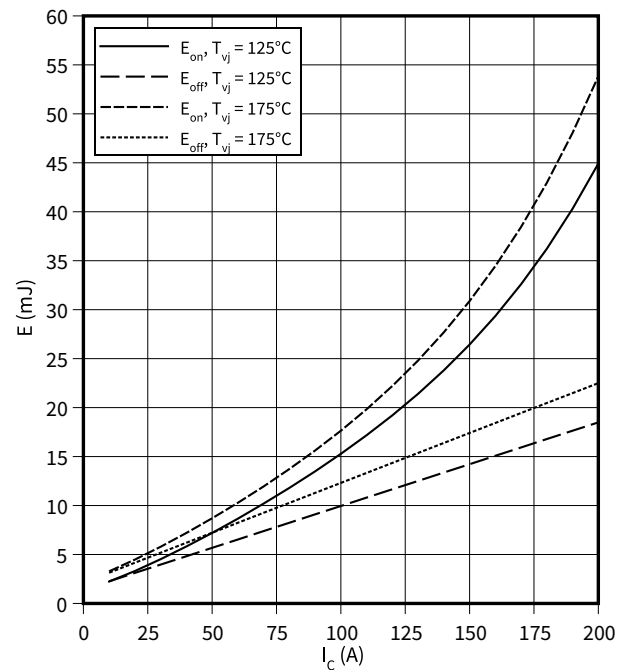
**transfer characteristic (typical), IGBT, Inverter**

$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



**switching losses (typical), IGBT, Inverter**

$E = f(I_C)$   
 $R_{Goff} = 4.3\ \Omega$ ,  $R_{Gon} = 4.3\ \Omega$ ,  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$

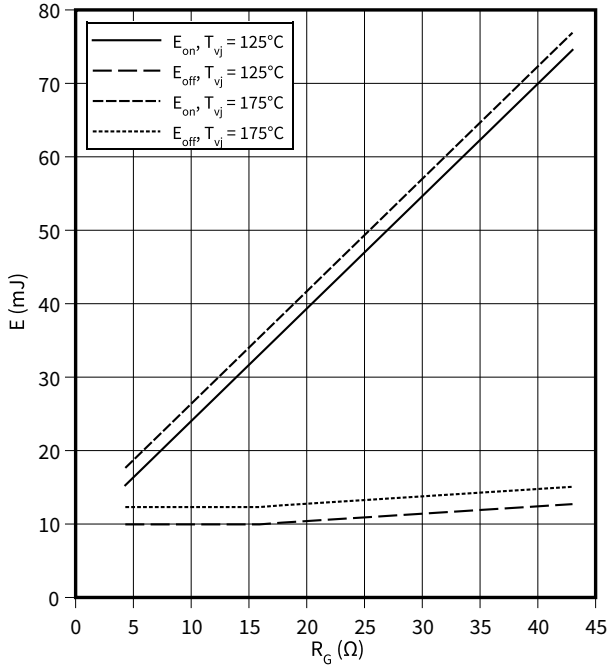


8 Characteristics diagrams

**switching losses (typical), IGBT, Inverter**

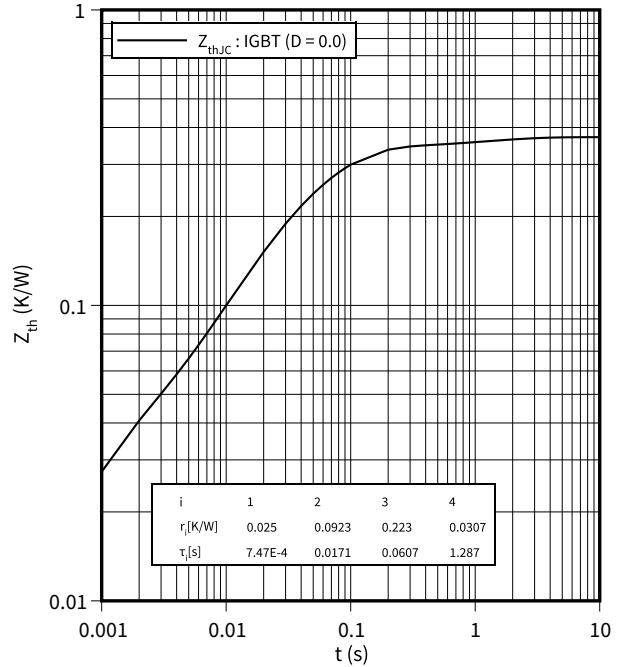
$E = f(R_G)$

$I_C = 100 \text{ A}$ ,  $V_{CE} = 600 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$



**transient thermal impedance, IGBT, Inverter**

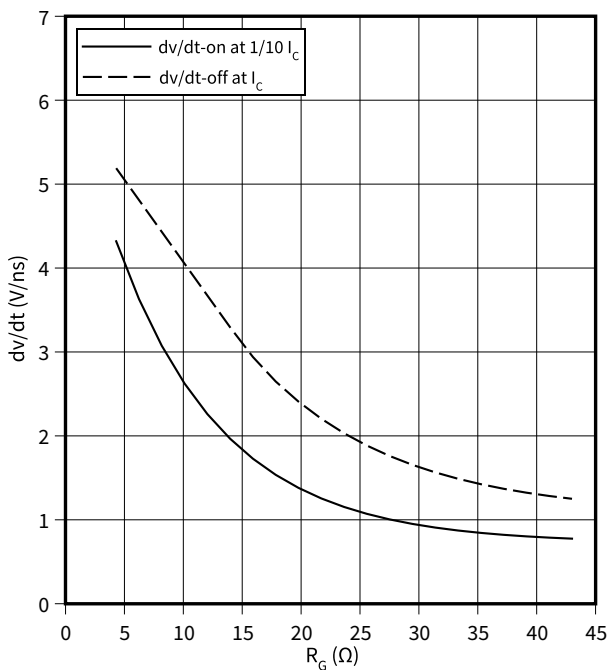
$Z_{th} = f(t)$



**Voltage slope (typical), IGBT, Inverter**

$dv/dt = f(R_G)$

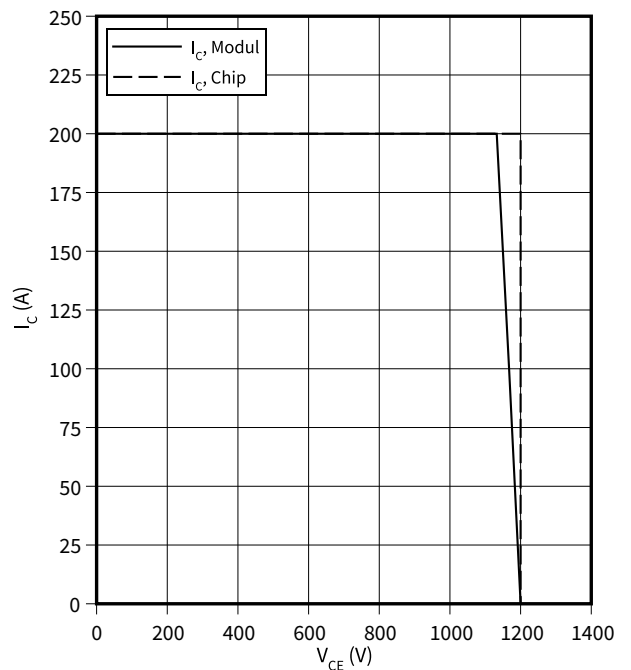
$I_C = 100 \text{ A}$ ,  $V_{CE} = 600 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $T_{vj} = 25 \text{ °C}$



**reverse bias safe operating area (RBSOA), IGBT, Inverter**

$I_C = f(V_{CE})$

$R_{Goff} = 4.3 \text{ } \Omega$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $T_{vj} = 175 \text{ °C}$

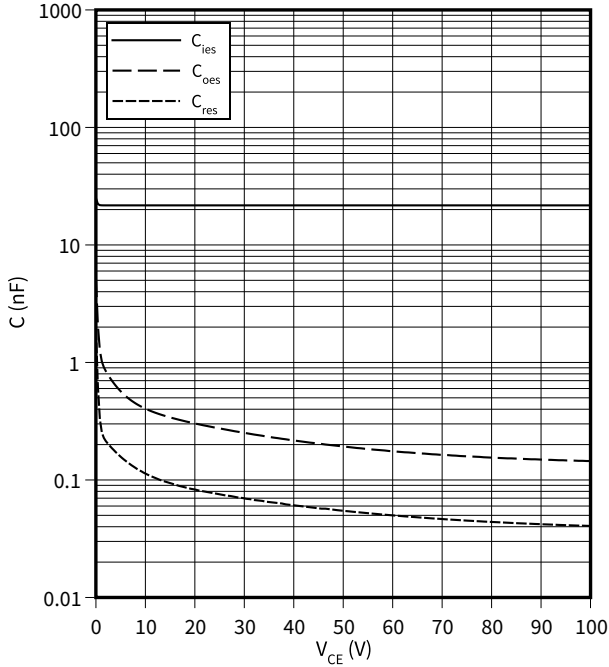


**8 Characteristics diagrams**

**capacity characteristic (typical), IGBT, Inverter**

$C = f(V_{CE})$

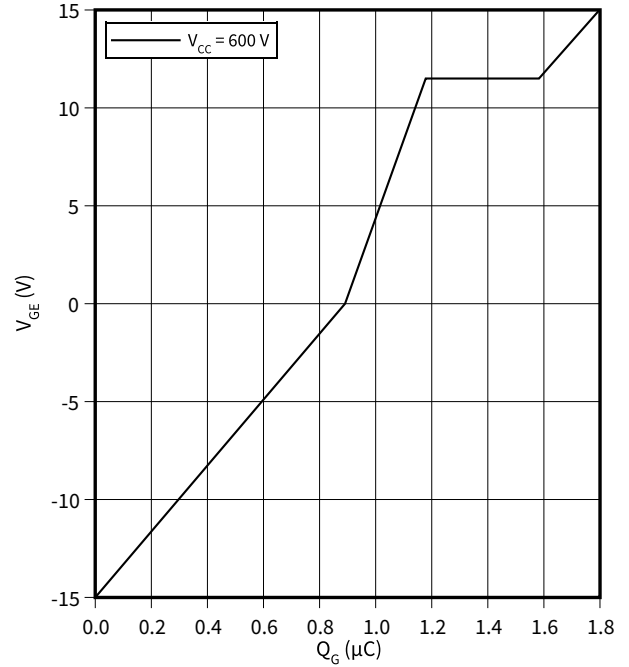
$f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$



**gate charge characteristic (typical), IGBT, Inverter**

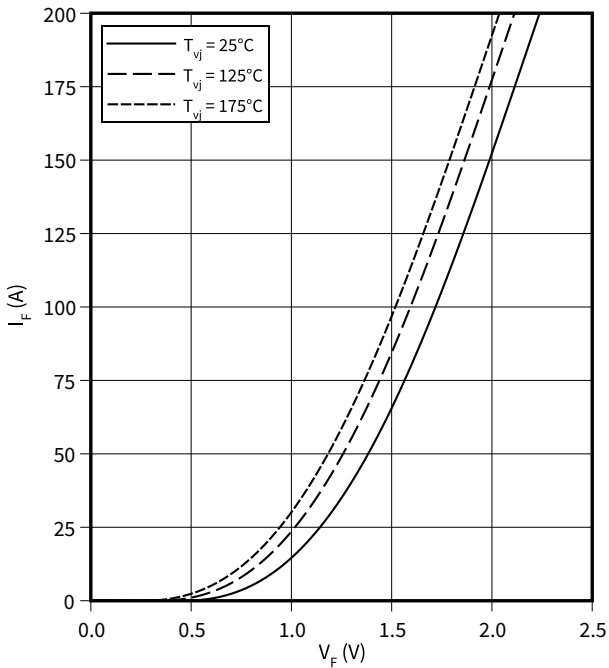
$V_{GE} = f(Q_G)$

$I_C = 100 \text{ A}, T_{vj} = 25 \text{ }^\circ\text{C}$



**forward characteristic of (typical), Diode, Inverter**

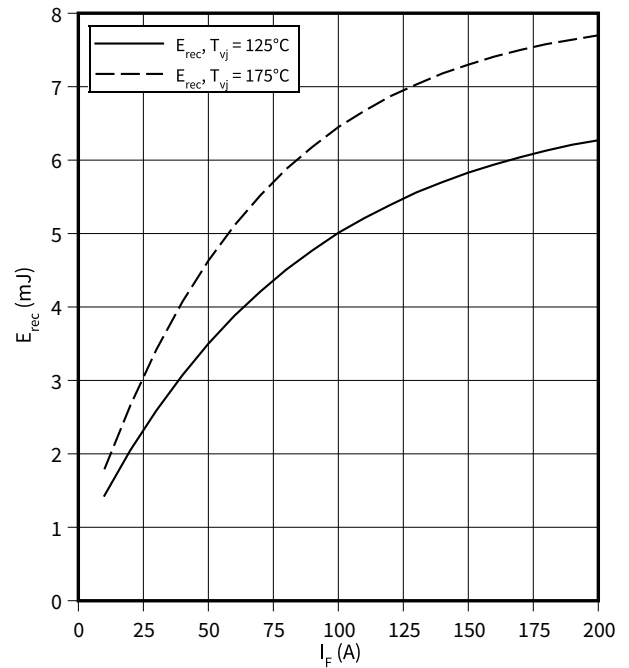
$I_F = f(V_F)$



**switching losses (typical), Diode, Inverter**

$E_{rec} = f(I_F)$

$R_{Gon} = 4.3 \text{ } \Omega, V_{CE} = 600 \text{ V}$

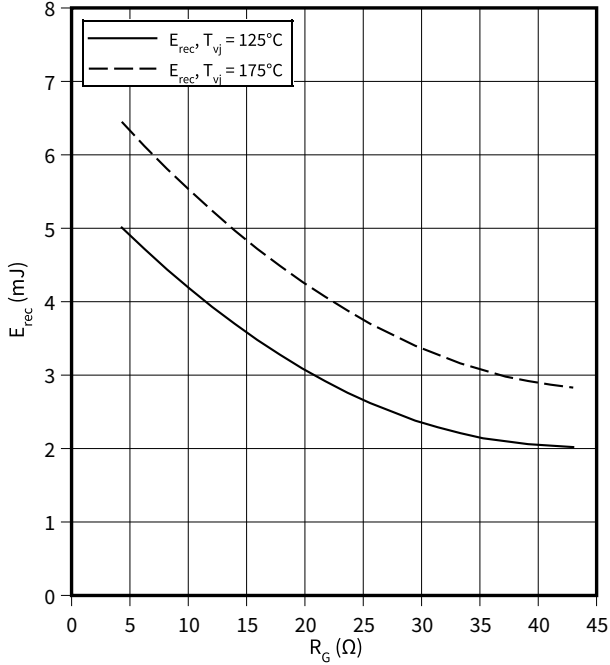


8 Characteristics diagrams

**switching losses (typical), Diode, Inverter**

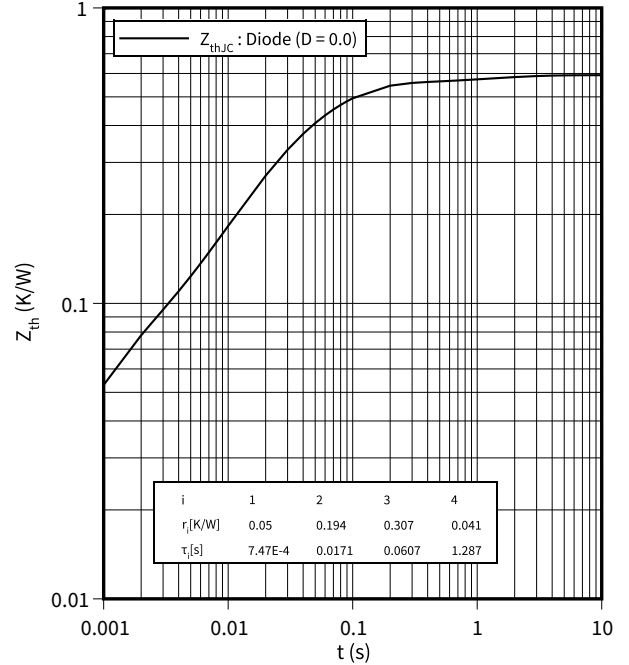
$E_{rec} = f(R_G)$

$V_{CE} = 600\text{ V}, I_F = 100\text{ A}$



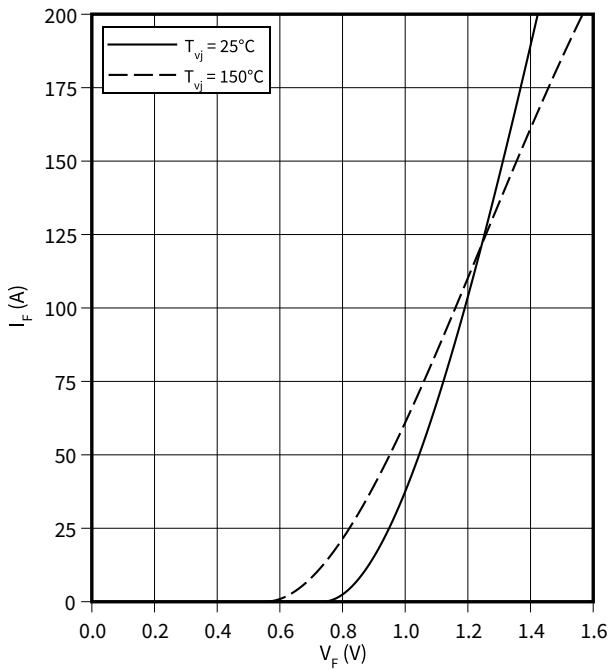
**transient thermal impedance, Diode, Inverter**

$Z_{th} = f(t)$



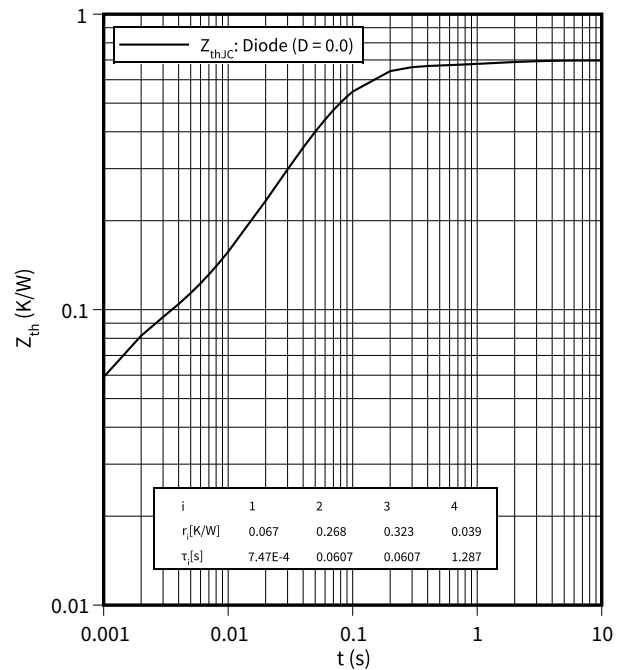
**forward characteristic of (typical), Diode, Rectifier**

$I_F = f(V_F)$



**transient thermal impedance, Diode, Rectifier**

$Z_{th} = f(t)$

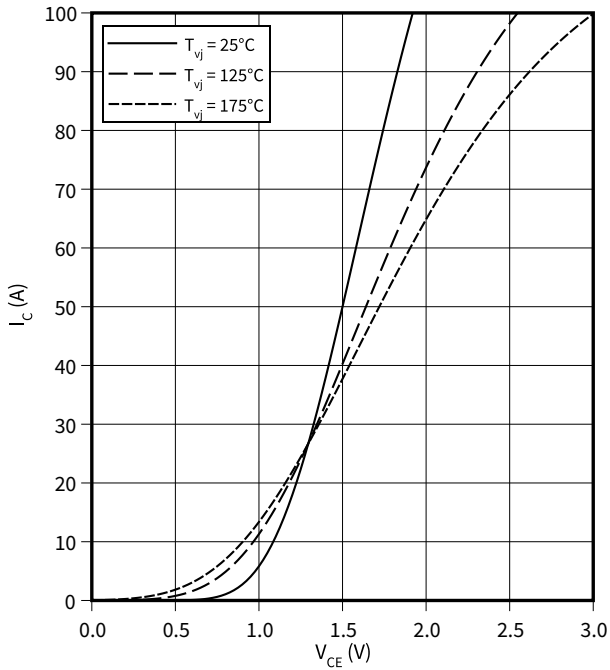


8 Characteristics diagrams

**output characteristic (typical), IGBT, Brake-Chopper**

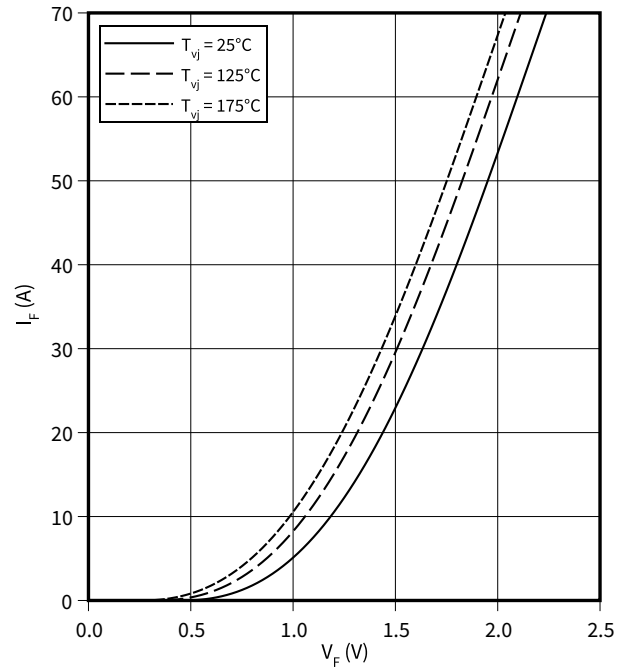
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



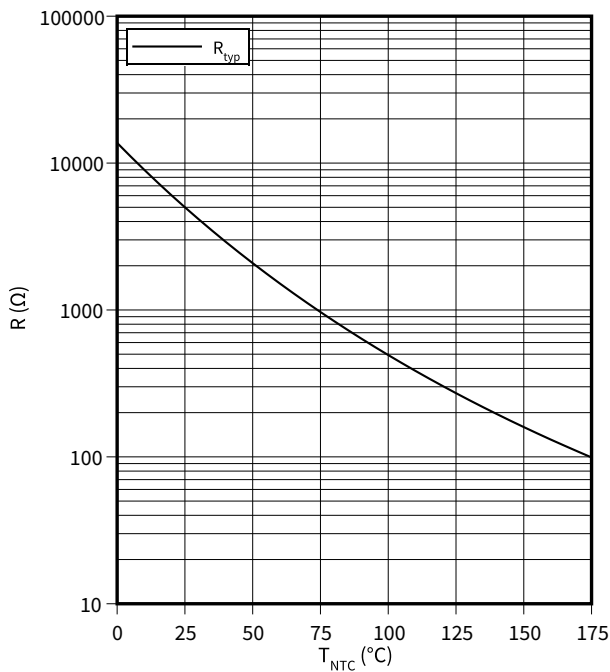
**forward characteristic of (typical), Diode, Brake-Chopper**

$I_F = f(V_F)$



**temperature characteristic (typical), NTC-Thermistor**

$R = f(T_{NTC})$



## 9 Circuit diagram

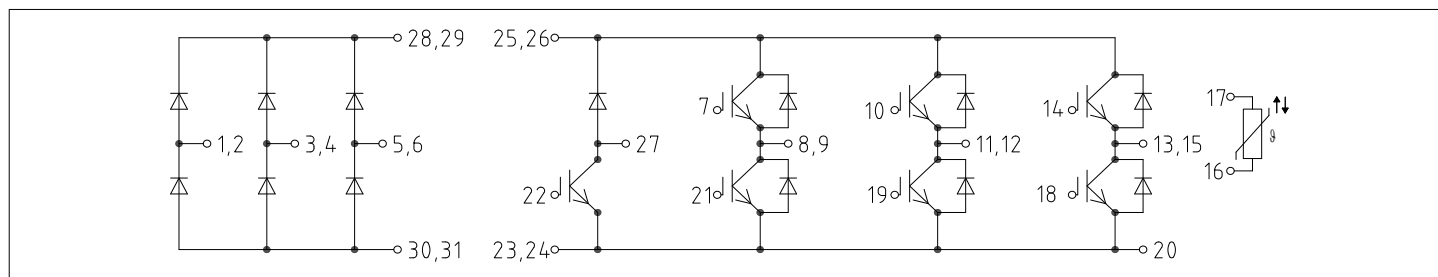
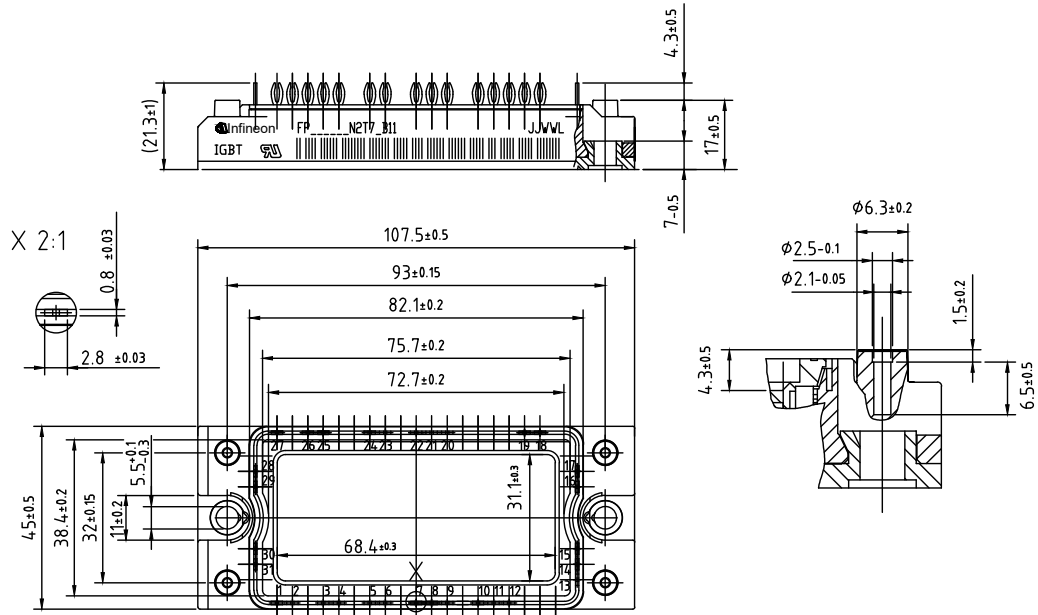


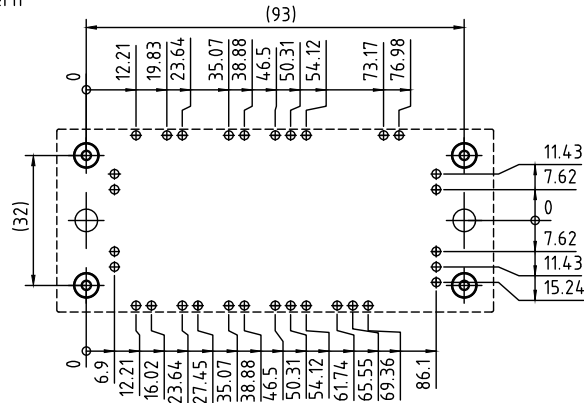
Figure 2



## 10 Package outlines



PCB hole pattern



- Tolerance of PCB hole pattern  $\varnothing \pm 0.1$
- hole specifications see AN 2007-09
- Diameters of plated holes  $\varnothing 2.14\text{mm} - 2.29\text{mm}$
- Diameter of drill  $\varnothing 2.35\text{mm}$

Figure 3

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Revision history

## Revision history

Document revision	Date of release	Description of changes
0.10	2021-09-21	Initial version

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**Document reference**

**IFX-ABB576-001**

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